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Vishay Semiconductors

# Medium Power Phase Control Thyristors (Stud Version), 50 A



PRIMARY CHARACTERISTICS				
I <sub>T(AV)</sub>	50 A			
$V_{DRM}/V_{RRM}$	100 V, 200 V, 400 V, 600 V, 800 V, 1000 V, 1200 V			
$V_{TM}$	1.60 V			
l <sub>GT</sub>	100 mA			
T <sub>J</sub>	-40 °C to 125 °C			
Package	TO-65 (TO-208AC)			
Circuit configuration	Single SCR			

#### **FEATURES**

- High current rating
- Excellent dynamic characteristics
- dV/dt = 1000 V/µs option
- Superior surge capabilities
- Standard package
- · Metric threads version available
- Types up to 1200 V V<sub>DRM</sub>/V<sub>RRM</sub>
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **TYPICAL APPLICATIONS**

- · Phase control applications in converters
- · Lighting circuits
- Battery charges
- Regulated power supplies and temperature and speed control circuit

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
1		50	Α		
I <sub>T(AV)</sub>	T <sub>C</sub>	94	°C		
I <sub>T(RMS)</sub>		80	Α		
I <sub>TSM</sub>	50 Hz	1430	۸		
	60 Hz	1490	Α		
I <sup>2</sup> t	50 Hz	10.18	kA <sup>2</sup> s		
1-1	60 Hz	9.30	KA-S		
V <sub>DRM</sub> /V <sub>RRM</sub>		100 to 1200	V		
t <sub>q</sub>	Typical	110	μs		
TJ		-40 to +125	°C		

## **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE <sup>(1)</sup> V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE <sup>(2)</sup> V	$\begin{aligned} I_{DRM}/I_{RRM} & \text{MAXIMUM AT} \\ & T_J = T_J & \text{MAXIMUM} \\ & \text{mA} \end{aligned}$			
	10	100	150				
	20	200	300				
	40	400	500				
VS-50RIA	60	600	700	15			
	80	800	900				
	100	1000	1100				
	120	1200	1300				

#### Notes

<sup>(1)</sup> Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs

 $<sup>\</sup>ensuremath{^{(2)}}$  For voltage pulses with  $t_p \leq 5 \ ms$ 



ABSOLUTE MAXIMUM RATII	NGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average on-state current	<b>I</b>	180° einueoi	180° sinusoidal conduction		50	Α
at case temperature	I <sub>T(AV)</sub>	100 3110301	dai conduction		94	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>				80	Α
		t = 10 ms	No voltage		1430	
Maximum peak, one-cycle	l=a	t = 8.3 ms	reapplied		1490	Α
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		1200	A
		t = 8.3 ms	reapplied	Sinusoidal half wave,	1255	
Maximum I <sup>2</sup> t for fusing		t = 10 ms	No voltage	initial $T_J = T_J$ maximum	10.18	- kA <sup>2</sup> s
	l <sup>2</sup> t	t = 8.3 ms	reapplied		9.30	
		t = 10 ms	100 % V <sub>RBM</sub>		7.20	
		t = 8.3 ms	reapplied		6.56	
Maximum $I^2\sqrt{t}$ for fusing	I <sup>2</sup> √t	$t = 0.1$ to 10 ms, no voltage reapplied, $T_J = T_J$ maximum		101.8	kA²√s	
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum		0.94	V	
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(\pi \times I_{T(AV)} < I < 20 \times \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		1.08	V	
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum		4.08	mΩ	
High level value of on-state slope resistance	r <sub>t2</sub>	$(\pi \times I_{T(AV)} < I < 20 \times \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$ 3.34		11152		
Maximum on-state voltage	$V_{TM}$	I <sub>pk</sub> = 157 A, T <sub>J</sub> = 25 °C		1.60	V	
Maximum holding current	I <sub>H</sub>	$T_J$ = 25 °C, anode supply 22 V, resistive load, initial $I_T$ = 2 A		200	mA	
Latching current	ال	Anode supp	ly 6 V, resistive lo	pad	400	

SWITCHING						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum rate of	$V_{DRM} \le 600 \text{ V}$	dl/dt	$T_C$ = 125 °C, $V_{DM}$ = Rated $V_{DRM},$ Gate pulse = 20 V, 15 $\Omega,$ $t_p$ = 6 $\mu s,$ $t_r$ = 0.1 $\mu s$ maximum $I_{TM}$ = (2 x rated dI/dt) A	200	- A/μs	
rise of turned-on current V <sub>D</sub>	$V_{DRM} \leq 1600 \; V$	di/dt		100		
Typical delay time		t <sub>d</sub>	$T_C$ = 25 °C, $V_{DM}$ = Rated $V_{DRM}$ , $I_{TM}$ = 10 A dc resistive circuit Gate pulse = 10 V, 15 $\Omega$ source, $t_p$ = 20 $\mu$ s	0.9		
Typical turn-off time		tq	$T_C$ = 125 °C, $I_{TM}$ = 50 A, reapplied dV/dt = 20 V/ $\mu$ s dIr/dt = -10 A/ $\mu$ s, $V_R$ = 50 V	110	μs	

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum critical rate of rise of	dV/dt	$T_J = T_J$ maximum linear to 100 % rated $V_{DRM}$	200	1//40	
off-state voltage	av/at	T <sub>J</sub> = T <sub>J</sub> maximum linear to 67 % rated V <sub>DRM</sub>	500 <sup>(1)</sup>	V/µs	

## Note

 $<sup>^{(1)}</sup>$  Available with dV/dt = 1000 V/ $\mu s$ , to complete code add S90 i.e. 50RIA120S90



TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak gate power	P <sub>GM</sub>	$T_J = T_J$ maximum, $t_p \le \xi$	ō ms	10	w
Maximum average gate power	P <sub>G(AV)</sub>			2.5	VV
Maximum peak positive gate current	I <sub>GM</sub>			2.5	А
Maximum peak positive gate voltage	+V <sub>GM</sub>			20	V
Maximum peak negative gate voltage	-V <sub>GM</sub>			10	V
	I <sub>GT</sub>	T <sub>J</sub> = - 40 °C	Maximum required gate trigger current/voltage are the lowest value which will trigger all units 6 V	250	mA
DC gate current required to trigger		T <sub>J</sub> = 25 °C		100	
		T <sub>J</sub> = 125 °C		50	
	.,,	T <sub>J</sub> = - 40 °C	anode to cathode applied	3.5	V
DC gate voltage required to trigger	V <sub>GT</sub>	T <sub>J</sub> = 25 °C		2.5	V
DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = T <sub>J</sub> maximum, V <sub>DRM</sub> = Rated voltage	Maximum gate current/voltage not to trigger is the maximum	5.0	mA
DC gate voltage not to trigger	$V_{\mathrm{GD}}$	$T_J = T_J \text{ maximum}$	value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.2	V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C	
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	0.35	K/W	
Maximum thermal resistance, case to heat sink	R <sub>thCS</sub>	CS Mounting surface, smooth, flat and greased		TV/VV	
Allowable mounting targue		Non-lubricated threads	3.4 + 0 - 10 % (30)	N · m	
Allowable mounting torque		Lubricated threads	2.3 + 0 - 10 % (20)	(lbf·in)	
Approximate weight			28	g	
Approximate weight			1.0	OZ.	
Case style		See dimensions - link at the end of datasheet TO-65 (TO-208AC)			

△R <sub>thJC</sub> CONDUCTION							
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS			
180°	0.078	0.057					
120°	0.094	0.098					
90°	0.120	0.130	$T_J = T_J$ maximum	K/W			
60°	0.176	0.183					
30°	0.294	0.296					

#### Note

The table above shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC

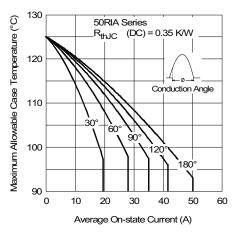


Fig. 1 - Current Ratings Characteristics

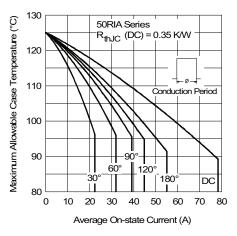


Fig. 2 - Current Ratings Characteristics

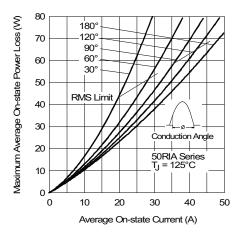


Fig. 3 - On-State Power Loss Characteristics

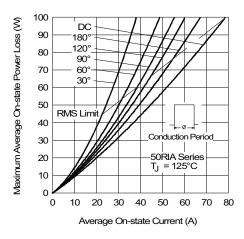


Fig. 4 - On-State Power Loss Characteristics

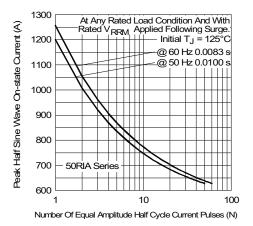


Fig. 5 - Maximum Non-Repetitive Surge Current

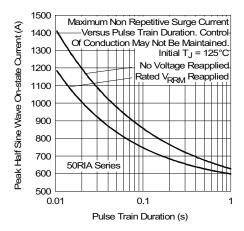


Fig. 6 - Maximum Non-Repetitive Surge Current

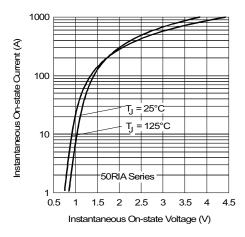


Fig. 7 - Forward Voltage Drop Characteristics

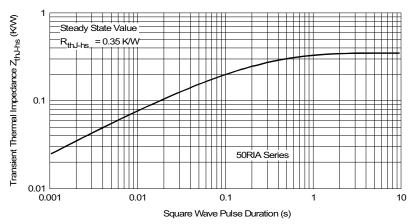


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics

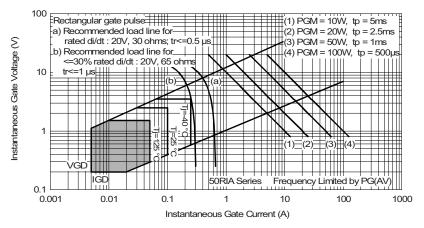
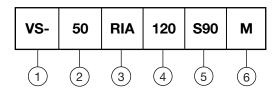


Fig. 9 - Gate Characteristics



## **ORDERING INFORMATION TABLE**

### **Device code**



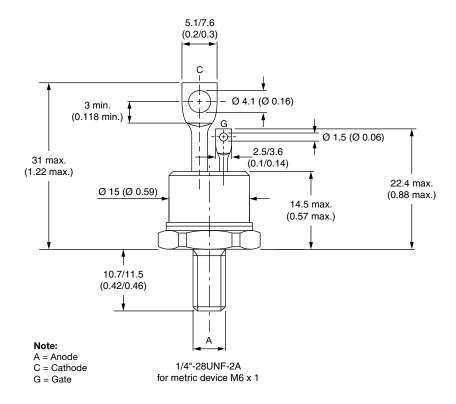
- Vishay Semiconductors product
- 2 Current code
- Essential part number
- Voltage code x 10 = V<sub>RRM</sub> (see Voltage Ratings table)
- 5 Critical dV/dt:
  - None = 500 V/µs (standard value)
  - S90 = 1000 V/µs (special selection)
- 6 • None = stud base TO-65 (TO-208AC) 1/4" 28UNF-2A
  - M = stud base TO-65 (TO-208AC) M6 x 1

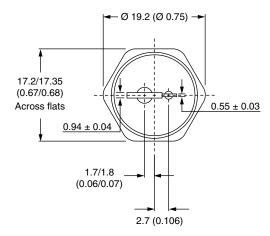
LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95334		



# TO-208AC (TO-65)

## **DIMENSIONS** in millimeters (inches)







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